# **BLF6G22L-40P**; Power LDMOS transistor Rev. 2 — 1 September 2015

**AMPLEON** 

Product data sheet

# **Product profile**

### 1.1 General description

LDMOS power transistor for base station applications at frequencies from 2110 MHz to 2170 MHz and 1805 MHz to 1880 MHz.

Table 1. Typical performance

Typical RF performance at  $T_{case} = 25$  °C in a common source class-AB production test circuit.

Mode of operation	f	I <sub>Dq</sub>	V <sub>DS</sub>	P <sub>L(AV)</sub>	Gp	$\eta_{D}$	ACPR
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)
2-carrier W-CDMA	2110 to 2170	410	28	13.5	19	30	-30 <u>[2]</u>
	1805 to 1880 [1]	410	28	5	20.3	18.3	-34.9 <sup>[2]</sup>
1-carrier W-CDMA	2110 to 2170	410	28	15	19	32	-37 <sup>[3]</sup>
	1805 to 1880 [1]	410	28	5	20.5	18.0	-42.3 [3]

<sup>[1]</sup> The performance is tested on the Class AB demo board as depicted in Figure 11.

### 1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low R<sub>th</sub> providing excellent thermal stability
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

### 1.3 Applications

- RF power amplifier for base stations and multi carrier applications in the 2110 MHz to 2170 MHz frequency band
- RF driver amplifier in the 1805 MHz to 1880 MHz frequency band

<sup>[2]</sup> Test signal: 3GPP; test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF; carrier spacing 5 MHz.

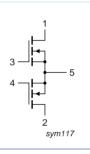
<sup>[3]</sup> Test signal: 3GPP; test model 1; 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF.

# 2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
BLF6G22	2L-40P (SOT1121A)			
1	drain1			
2	drain2		1 2 [~] [~]	1 اـــا.
3	gate1			3
4	gate2			5
5	source	<u>[1]</u>	3 4	4
				' <b>└</b>
				2 sym117

BLF6G22LS-4	40P (SOT1121B)	
1	drain1	
2	drain2	
3	gate1	
4	gate2	
5	source	[1]



# 3. Ordering information

Table 3. Ordering information

Type number	Packa	kage		
	Name	Description	Version	
BLF6G22L-40P	-	flanged LDMOST ceramic package; 2 mounting holes; 4 leads	SOT1121A	
BLF6G22LS-40P	-	earless flanged LDMOST ceramic package; 4 leads	SOT1121B	

# 4. Limiting values

Table 4. Limiting values (2 sections combined)

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	65	V
$V_{GS}$	gate-source voltage		-0.5	+13	V
$I_D$	drain current		-	16	Α
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	200	°C

<sup>[1]</sup> Connected to flange.

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-c)</sub>	thermal resistance from junction to case	$T_{case}$ = 80 °C; $P_L$ = 40 W	0.7	K/W

### 6. Characteristics

Table 6. Characteristics (per section)

 $T_i = 25$  °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_{D} = 0.4 \text{ mA}$	65	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_{D} = 40 \text{ mA}$	1.4	1.9	2.4	V
I <sub>DSS</sub>	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}$	-	-	2	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	6	7	-	Α
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 11 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	200	nA
g <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_{D}$ = 2.0 A	1.8	2.9	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 1.4 \text{ A}$	0.14	0.37	0.57	Ω

# 7. Application information

Table 7. Application information (2 sections combined)

Mode of operation: 2-carrier W-CDMA; PAR 8.4 dB at 0.01 % probability on CCDF; 3GPP test model 1; 64 DPCH;  $f_1$  = 2112.5 MHz;  $f_2$  = 2117.5 MHz;  $f_3$  = 2162.5 MHz;  $f_4$  = 2167.5 MHz; RF performance at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 410 mA;  $I_{Case}$  = 25 °C; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	$P_{L(AV)} = 13.5 \text{ W}$	<u>11</u> 17.8	19	-	dB
RLin	input return loss	$P_{L(AV)} = 13.5 \text{ W}$	[1] -	-15	-9	dB
$\eta_{D}$	drain efficiency	$P_{L(AV)} = 13.5 \text{ W}$	<u>11</u> 26.5	30	-	%
ACPR <sub>5M</sub>	adjacent channel power ratio (5 MHz)	$P_{L(AV)} = 13.5 \text{ W}$	[1] -	-30	-27	dBc
ACPR <sub>10M</sub>	adjacent channel power ratio (10 MHz)	$P_{L(AV)} = 13.5 \text{ W}$	<u>[1]</u> -	-39	-36	dBc

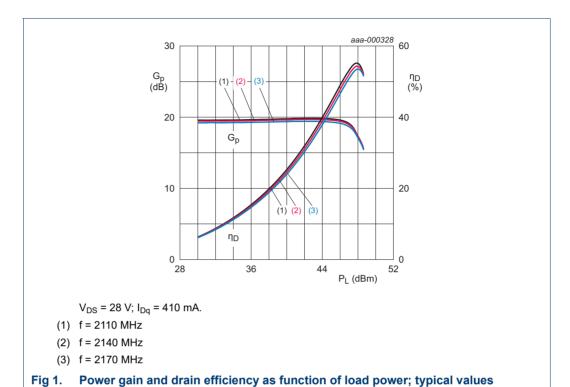
<sup>[1]</sup> In production, all testing are only performed at 2110 MHz to 2170 MHz frequency band.

### 7.1 Ruggedness in class-AB operation

The BLF6G22L-40P and BLF6G22LS-40P are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS} = 28 \text{ V}$ ;  $I_{Dq} = 410 \text{ mA}$ ;  $P_L = 40 \text{ W}$  (CW); f = 2110 MHz.

The BLF6G22L-40P and BLF6G22LS-40P are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS} = 28 \text{ V}$ ;  $I_{Dq} = 410 \text{ mA}$ ;  $P_L = 40 \text{ W}$  (CW pulse, 10 %); f = 1842 MHz.

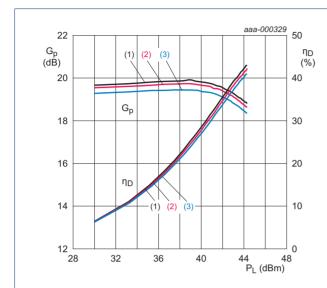
### 7.2 CW



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### 7.3 IS-95

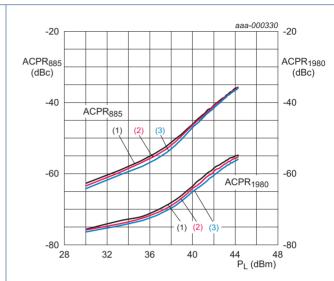
Single carrier IS-95; PAR = 9.7 dB at 0.01 % probability on the CCDF.



 $V_{DS} = 28 \text{ V}; I_{Dq} = 410 \text{ mA}.$ 

- (1) f = 2110 MHz
- (2) f = 2140 MHz
- (3) f = 2170 MHz

Fig 2. Single carrier IS-95 power gain and drain efficiency as function of output power; typical values



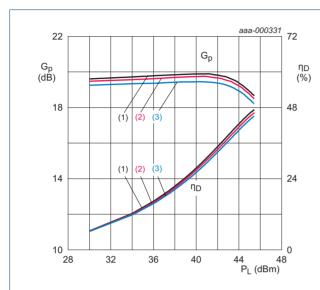
 $V_{DS} = 28 \text{ V}; I_{Dq} = 410 \text{ mA}.$ 

- (1) f = 2110 MHz
- (2) f = 2140 MHz
- (3) f = 2170 MHz

Fig 3. Single carrier IS-95 adjacent channel power ratio as a function of output power; typical values

### 7.4 1-carrier W-CDMA

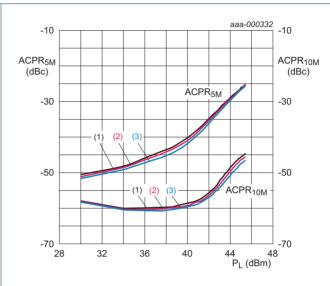
Test signal: 3GPP; test model 1; 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF.



 $V_{DS} = 28 \text{ V}; I_{Dq} = 410 \text{ mA}.$ 

- (1) f = 2112.5 MHz
- (2) f = 2140 MHz
- (3) f = 2167.5 MHz

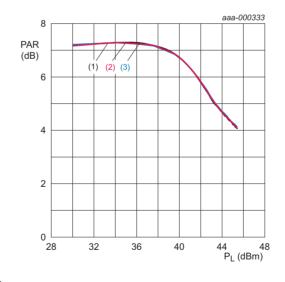
Fig 4. 1-carrier W-CDMA power gain and drain efficiency as function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 410 \text{ mA}.$ 

- (1) f = 2112.5 MHz
- (2) f = 2140 MHz
- (3) f = 2167.5 MHz

Fig 5. 1-carrier W-CDMA adjacent channel power ratio as a function of output power; typical values



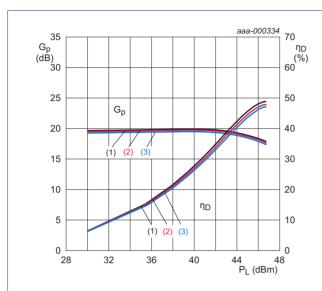
 $V_{DS} = 28 \text{ V}; I_{Dq} = 410 \text{ mA}.$ 

- (1) f = 2112.5 MHz
- (2) f = 2140 MHz
- (3) f = 2167.5 MHz

Fig 6. 1-carrier W-CDMA power gain and drain efficiency as function of output power; typical values

#### 7.5 2-carrier W-CDMA

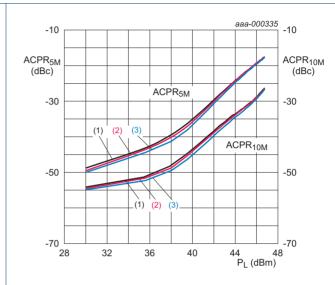
Test signal: 3GPP; test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF; carrier spacing 5 MHz.



 $V_{DS} = 28 \text{ V}; I_{Dq} = 410 \text{ mA}.$ 

- (1) f = 2115 MHz
- (2) f = 2140 MHz
- (3) f = 2165 MHz

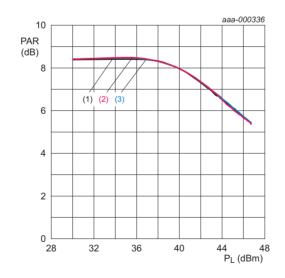
Fig 7. 2-carrier W-CDMA power gain and drain efficiency as function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 410 \text{ mA}.$ 

- (1) f = 2115 MHz
- (2) f = 2140 MHz
- (3) f = 2165 MHz

Fig 8. 2-carrier W-CDMA adjacent channel power ratio as a function of output power; typical values

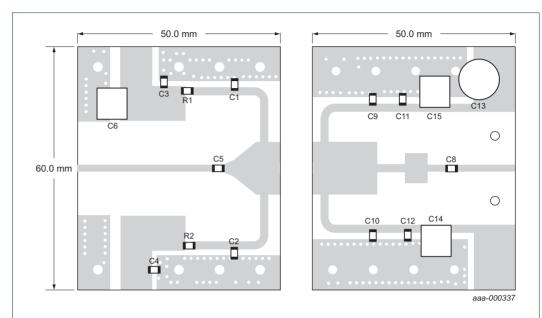


 $V_{DS} = 28 \text{ V}; I_{Dq} = 410 \text{ mA}.$ 

- (1) f = 2115 MHz
- (2) f = 2140 MHz
- (3) f = 2165 MHz

Fig 9. 2-carrier W-CDMA peak-to-average power ratio as function of output power; typical values

## 8. Test information



Printed-Circuit Board (PCB): Rogers RO4350;  $\epsilon_{r}$  = 3.5 F/m; thickness = 0.762 mm; thickness copper plating = 35  $\mu$ m.

The vias can be as a reference to place components.

The above layout shows the test circuit used to measure the devices in production. A more appropriate application demonstration for specific customer needs can be provided.

See Table 8 for list of components.

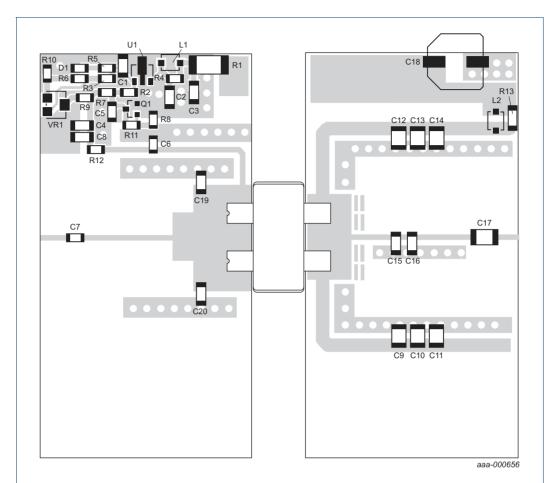
Fig 10. Component layout

**Table 8.** List of components
See Figure 10 for component layout.

Component	Description	Value	Remarks
C1, C2, C9, C10	multilayer ceramic chip capacitor	68 pF	<u>[1]</u>
C3, C4, C11, C12	multilayer ceramic chip capacitor	820 pF	<u>[2]</u>
C5, C8	multilayer ceramic chip capacitor	4.7 pF	<u>[1]</u>
C6, C14, C15	multilayer ceramic chip capacitor	10 μF	TDK
C13	electrolytic capacitor	470 μF; 63 V	
R1, R2	chip resistor	12 Ω	Philips 1206

<sup>[1]</sup> American Technical Ceramics type 800B or capacitor of same quality.

<sup>[2]</sup> American Technical Ceramics type 100A or capacitor of same quality.



Printed-Circuit Board (PCB): Rogers RO4350;  $\epsilon_{\text{r}}$  = 3.5 F/m; thickness = 0.762 mm; thickness copper plating = 35  $\mu$ m.

The vias can be as a reference to place components.

The above layout shows the test circuit used to measure the devices in production. A more appropriate application demonstration for specific customer needs can be provided.

See Table 9 for list of components.

Fig 11. 1.8 GHz Demo board layout

**Table 9.** List of components
See Figure 11 for component layout.

Component	Description	Value	Remarks
C1, C2, C5, C8	multilayer ceramic chip capacitor	100 nF	Murata
C3, C4, C11, C14	multilayer ceramic chip capacitor	1 μF	Murata
C6	multilayer ceramic chip capacitor	47 pF	ATC
C7	multilayer ceramic chip capacitor	10 pF	ATC
C9, C12	multilayer ceramic chip capacitor	12 pF	ATC
C10, C13	multilayer ceramic chip capacitor	330 pF	Murata
C15, C16	multilayer ceramic chip capacitor	1.5 pF	ATC
C17	multilayer ceramic chip capacitor	10 pF	ATC
C18	electrolytic capacitor	2200 μF, 50 V	Panasonic
C19, C20	multilayer ceramic chip capacitor	1 pF	ATC

BLF6G22L-40P\_6G22LS-40P#2

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**Power LDMOS transistor** 

**Table 9.** List of components
See Figure 11 for component layout.

Component	Description	Value	Remarks
L1, L2	ferrite bead	5 A	Fair Rite
R1	chip resistor	500 Ω	Vishay Dale
R2, R5	chip resistor	1.1 kΩ	Vishay Dale
R3, R6	chip resistor	432 Ω	Vishay Dale
R4, R11	chip resistor	9.1 Ω	Vishay Dale
R9	chip resistor	2 kΩ	Vishay Dale
R10	chip resistor	75 Ω	Vishay Dale
R12	chip resistor	1.5 Ω	Vishay Dale
VR1	potentiometer	200 Ω	Bourns
U1	voltage regulator		NJR

# 9. Package outline

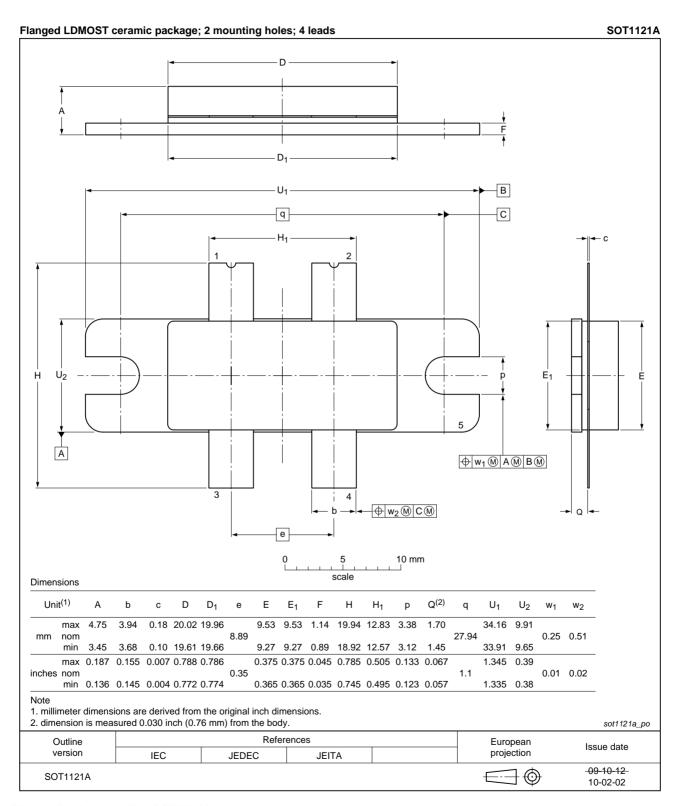


Fig 12. Package outline SOT1121A

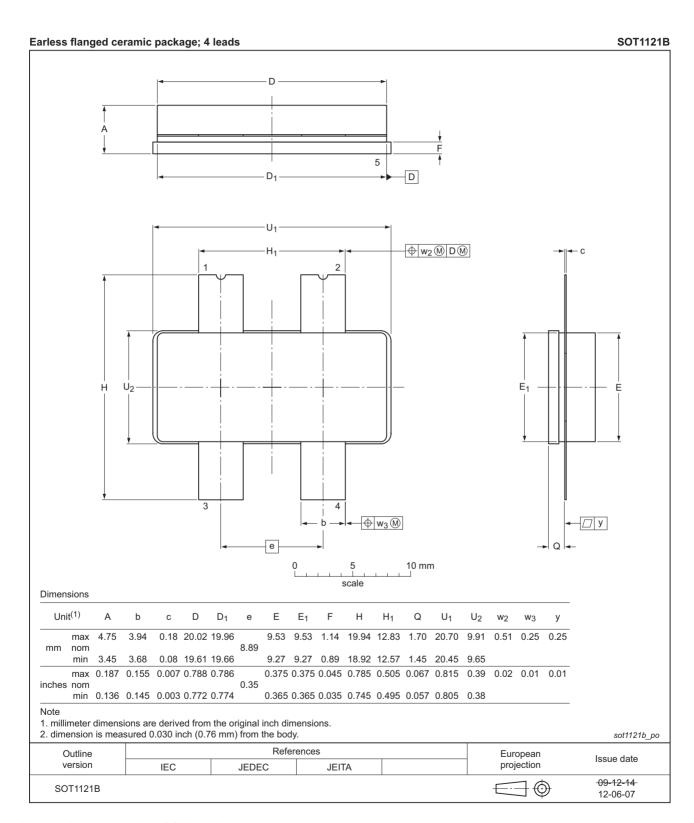


Fig 13. Package outline SOT1121B

**Power LDMOS transistor** 

# 10. Abbreviations

Table 10. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
IS-95	Interim Standard 95
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LDMOST	Laterally Diffused Metal Oxide Semiconductor Transistor
PAR	Peak-to-Average power Ratio
RF	Radio Frequency
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

# 11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLF6G22L-40P_6G22LS-40P#2	20150901	Product data sheet	-	BLF6G22L-40 P_6G22LS-40 P v.1	
Modifications:	The format of this document has been redesigned to comply with the new identity guidelines of Ampleon.				
	<ul> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>				
BLF6G22L-40P_6G22LS-40P v.1	20110922	Product data sheet	-	-	

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### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
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Product [short] data sheet	Production	This document contains the product specification.

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